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	Complet if Known		
Substitute for form 1449A/B/PTO	Application Number	Unknown	
	Filing Date	December 11, 2001	
INFORMATION DISCLOSURE	First Named Inventor	IZUO	
STATEMENT BY APPLICANT	Group Art Unit	Unknown	
	Examiner Name	Unknown	
(Use as many sheets as necessary) Sheet 1 of 1	Attorney Docket Number	401479/AOYAMA	

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^{*} A concise statement of relevance is being submitted in lieu of a translation. 37 CFR 1.98(a)(3).

+ An English-language equivalent/patent, or an English-language abstract, or an English-language version of the search report or action by a foreign patent office in a counterpart foreign application indicating the degree of relevance found by the foreign office is being submitted in lieu of a concise explanation of relevance under 37 CFR 1.98(a)(3).